



Date: February , 2006
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(REV. 05/03) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO. NLI-002AX	APPLICATION NO. 10/092,033
	APPLICANT: Stephen F. Fulghum	
	FILING DATE 3/5/02	TC ART UNIT 3739

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION/ ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>JS</i>	US 4,852,579	8/1/89	Gilstad et al.	128	665	4/20/87
<i>JS</i>	US 5,298,741	3/29/94	Walt et al.	250	227	1/13/93
<i>JS</i>	US 5,989,181	11/23/99	Dutting et al.	600	108	11/10/97
	US					
	US					
	US					
	US					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

<i>h</i>	Han et al., "AlGaIn/GaN quantum well ultraviolet light emitting diodes", Applied Physics Letters, Vol. 73, No. 12, pp 1688-1690, 1998.

EXAMINER <i>JS</i> LEUBACKER	DATE CONSIDERED <i>3/16/06</i>
<small>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>	

***The art was cited in PCT International Search Report mailed January 18, 2006 in International Application No. PCT/US00/01673 filed January 26, 2000. A copy of the Int'l Search Report is enclosed.**

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